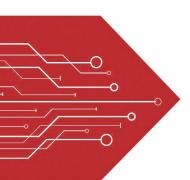
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Brodnet data speet

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FEATURES

- Low forward voltage
- · High current capability
- High forward surge capability
- Low power losses, High efficiency
- Guarding for over voltage protection

APPLICATIONS

Low VF Schottky barrier rectifier are designed for high frequency, miniature switched mode power supplies such as adapters, lighting and on-board DC/DC conerters

ME	CH	ΔΝ	$IC\Delta$	

Case: Molded plasticPolarity: As markedMounting Position: Any

 $\bullet \, \textbf{Molded Plastic:} \, \textbf{ULF} lamma bility Classification Rating 94 V-0$

 $\bullet \, Lead \, free \, in \, compliance \, with \, EU \, Ro HS \, 2011/65/EU \, directive$

Primary Characteristic			
lo	2*5A		
V_{RRM}	60V		
I _{FSM}	190A		
V _F	0.59V		
T₃max	150℃		
Assembly code	AC		

Maximum Ratings (Per Leg) at Ta=25°C unless otherwise specified				
Characteristics		Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage		V _{RRM}	60	V
Working Peak Reverse Voltage		V _{RWM}	60	V
Maximum DC Blocking Voltage		V _{DC}	60	V
Mariana Anna Francis Destification and	Per Leg	1.	5	۸
Maximum Average Forward Rectified Current	Total	lo	10	Α
Peak Forward Surge Current,8.3 ms Single Half Sine-wave		I _{FSM}	190	Α
Operating Temperature Range		TJ	150	°C
Storage Temperature Range		T _{STG}	-40 to +150	°C
TypicalThermalResistance(Note1)				
TO-220AB,TO-263,TO-252		R _{0 JC}	2	°C/W
TO-220F			4	
-				

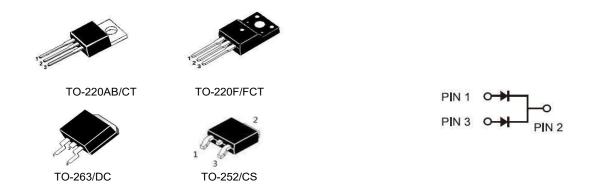
Note1: Thermal resistance from Junction to case per leg mounted on heatsink.

Electrical Characteristics (Per	Leg) unless o	otherwise	specified		
Characteristics		Symbol	Val	ue	Unit
Forward Voltage Drop(Note2)			Тур.	Max.	
at I _F =2A	TA=25°C	V _F	0.53	-	
at IF-ZA	TA=125°C		0.47	-	
at 1 = 2 A	TA=25°C		0.59	-	V
at I _F =3A	TA=125°C		0.52	-	
at I = E A	TA=25°C] [0.69	0.75	
at I _F =5A	TA=125°C		0.59	-	
Maximum Reverse Current at V _R =60V	TA=25°C		2	50	μΑ
Iviaximum Reverse Current at V _R =60V	TA=125°C	I _R	1.5	-	mA

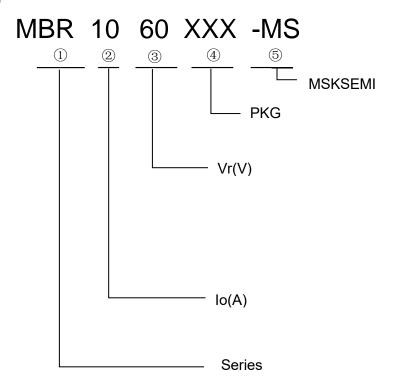
Note2:Pulse test: 300 µs pulse width, 1 % duty cycle



SCHOTTKY BARRIER RECTIFIER



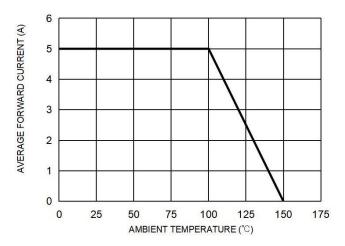
P/N Information



1)	2	3	4	(5)
系列	平均整流电流	直流反向耐压	封装	MSKSEMI

RATINGS AND CHARACTERISTIC CURVES

FIG.1 MAXIMUM FORWARD CURRENT DERATING CURVE



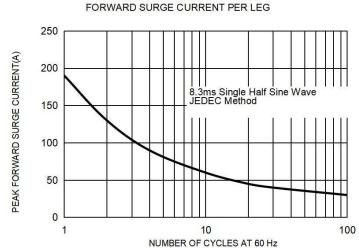
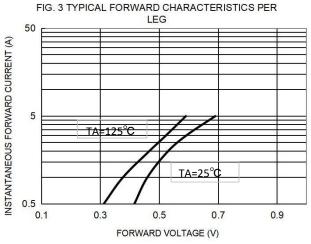
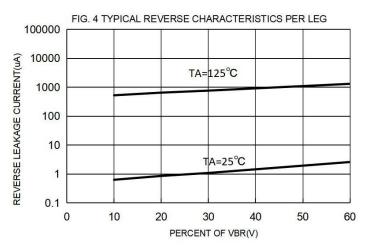
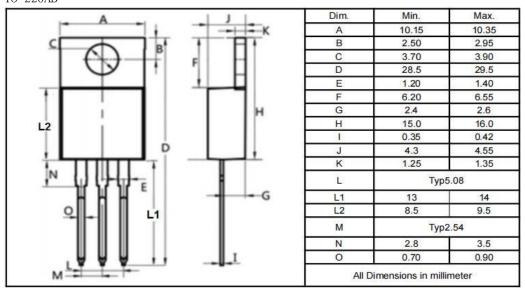


FIG. 2 MAXIMUM NON-REPETITIVE



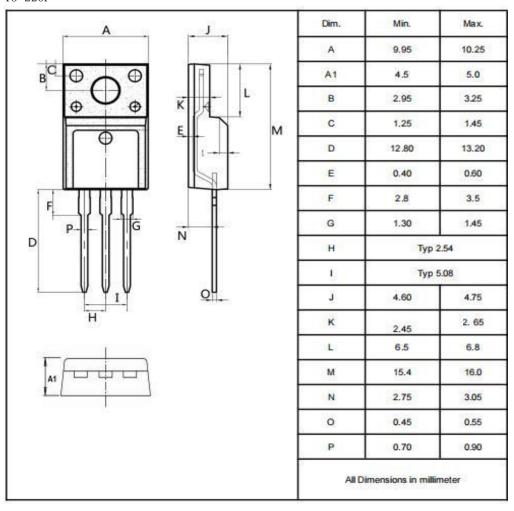


TO-220AB



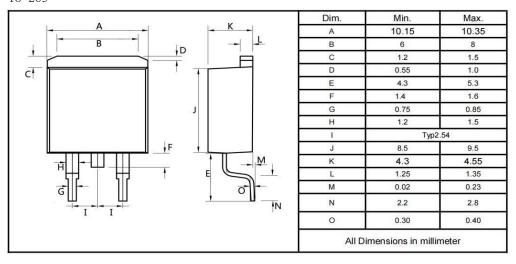
P/N	PKG	QTY
MBR1060CT-MS	TO-220AB	50pcs/tube 1000pcs/box

TO-220F



P/N	PKG	QTY
MBR1060FCT-MS	TO-220F	50pcs/tube 1000pcs/box

TO-263

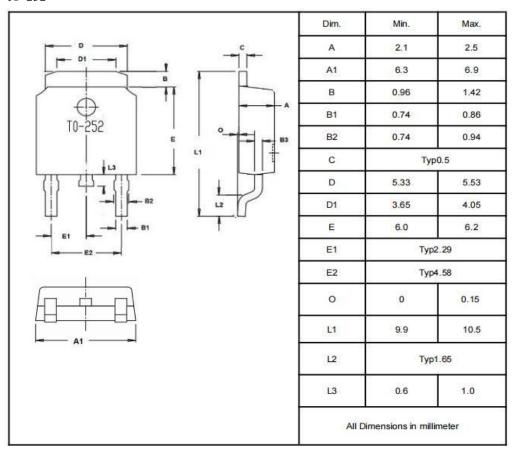


REEL SPECIFICATION

P/N	PKG	QTY
MBR1060DC-MS	TO-263	50pcs/tube 1000pcs/box

P/N	PKG	QTY
MBR1060DC-R-MS	TO-263	800pcs

TO-252



P/N	PKG	QTY
MBR1060CS-MS	TO-252	2500



Semiconductor

Compiance

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